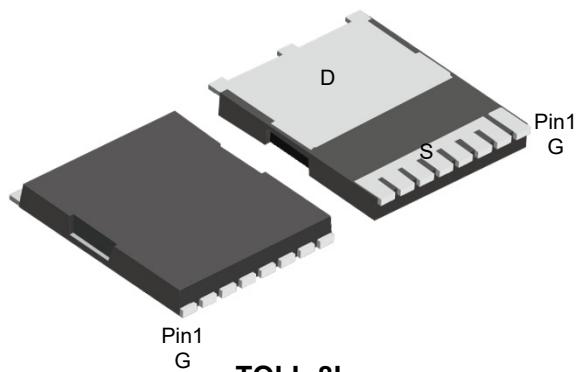


Description

The PSMLT04R1L uses split gate trench technology to provide excellent $R_{DS(ON)}$ low gate charge. This device is suitable for power management and high efficiency applications at high switching frequencies applications.

MOSFET Product Summary		
$V_{DS}(V)$	$R_{DS(on)}(m\Omega)$	$I_D(A)$
40	0.85@ $V_{GS} = 10V$	360



Feature

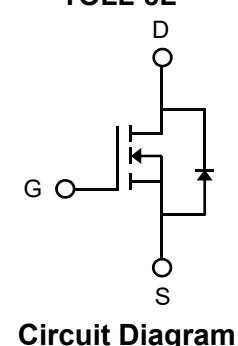
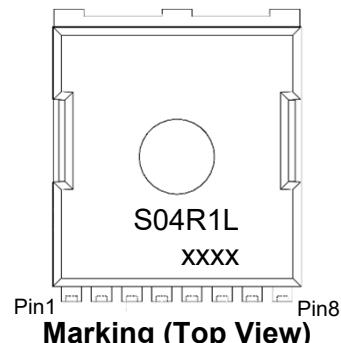
- Low $R_{DS(ON)}$ - Ensures On-State Losses are Minimized
- Excellent $Q_{gd} \times R_{DS(ON)}$ Product(FOM)
- Advanced Technology for DC-DC Converts
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- 100% UIS (Avalanche) Rated
- Lead-Free Finish ; RoHS Compliant
- Halogen and Antimony Free. "Green" Device

Applications

- PWM applications
- Load switch
- Power management
- DC-DC Converters
- Wireless Chargers

Absolute maximum rating@25°C

Rating	Symbol	Value	Units
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous ¹⁾	I_D	360	A
$T_C=100^\circ C$		230	
Pulsed Drain Current ²⁾	I_{DM}	1440	A
Total Power Dissipation ³⁾	P_D	290.7	W
Avalanche Current ⁴⁾	I_{AS}	88	A
Avalanche Energy ⁴⁾	E_{AS}	1161	mJ
Thermal Resistance , Junction-case ⁵⁾	$R_{\theta JC}$	0.4	°C/W
Thermal Resistance Junction-to-Ambient ⁶⁾	$R_{\theta JA}$	27.7	°C/W
Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	°C


Circuit Diagram

Marking (Top View)

Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	40	44	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 40V, V_{GS} = 0V$	-	-	1.0	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	± 100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.2	1.8	2.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 50A$	-	0.85	1.2	mΩ
		$V_{GS} = 4.5V, I_D = 50A$	-	1.25	1.7	
Dynamic Characteristics⁷⁾						
Input Capacitance	C_{iss}	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$	-	6300	-	pF
Output Capacitance	C_{oss}		-	1490	-	
Reverse Transfer Capacitance	C_{rss}		-	98	-	
Switching Characteristics⁷⁾						
Turn-on Delay Time	$t_{d(on)}$	$V_{DS} = 20V, V_{GS} = 10V, R_G = 4\Omega, I_D = 50A$	-	15	-	ns
Turn-on Rise Time	t_r		-	42	-	
Turn-Off Delay Time	$t_{d(off)}$		-	84	-	
Turn-Off Fall Time	t_f		-	72	-	
Total Gate Charge	Q_g	$V_{DS} = 32V, V_{GS} = 10V, I_D = 50A$	-	99.7	-	nC
Gate-Source Charge	Q_{gs}		-	20.5	-	
Gate-Drain Charge	Q_{gd}		-	17.8	-	
Gate Resistance	R_g	f=1MHz, Open Drain	-	1.2	-	Ω
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	$V_{GS} = 0V, I_S = 40A$	-	0.8	1.2	V

Notes:

1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. Repetitive Rating: Pulse width limited by maximum junction temperature($T_{J_Max}=150^{\circ}C$).
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. This single-pulse measurement was taken under the following condition [$L=0.3mH, V_{GS}=10V, V_{DS}=40V$]while it's value is limited by $T_{J_Max}=150^{\circ}C$
5. Device mounted on infinite heatsink
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout
7. Guaranteed by design, not subject to production

Typical Characteristics

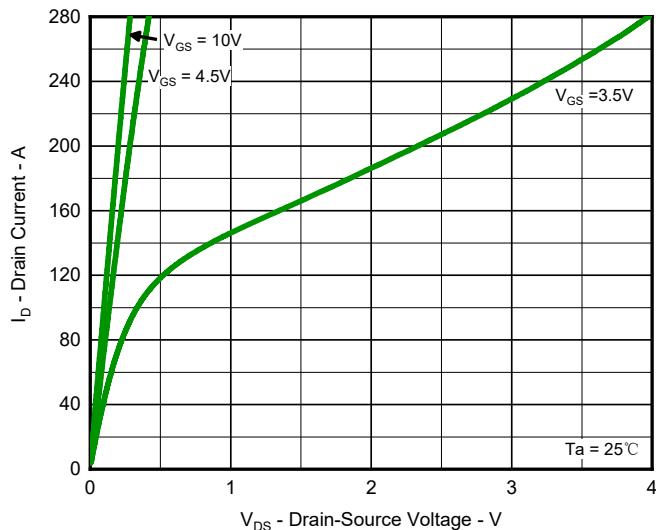


Fig.1 Output Characteristics

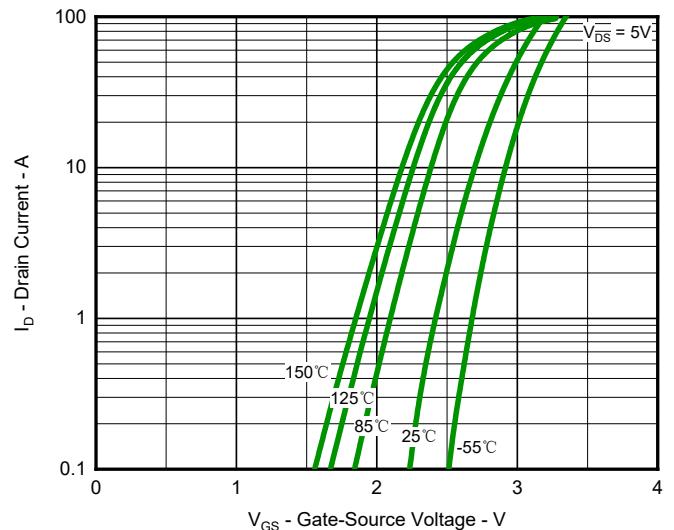


Fig.2 Typical Transfer Characteristic

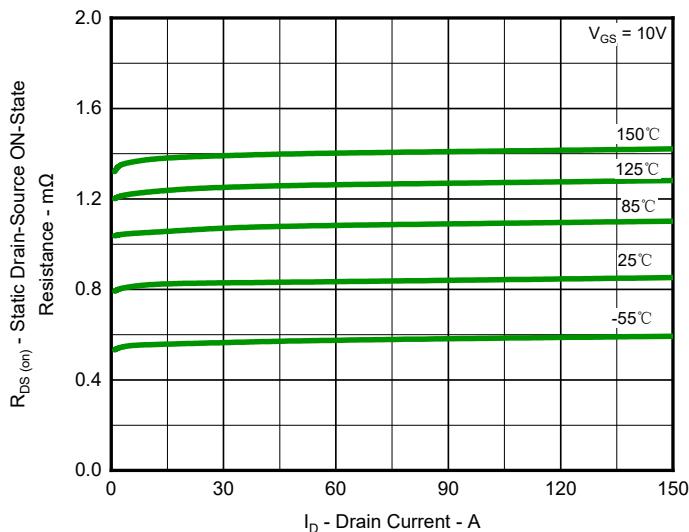


Fig.3 Typical On-Resistance vs Drain Current and Temperature

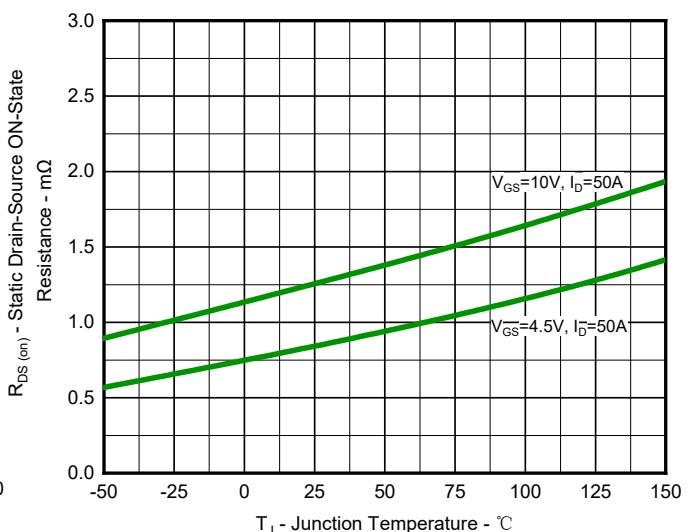


Fig.4 On-Resistance Variation with Temperature

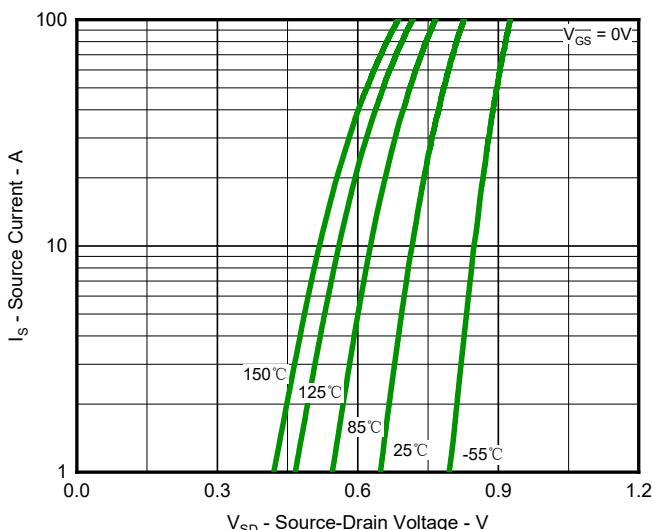


Fig.5 Diode Forward Voltage vs. Current

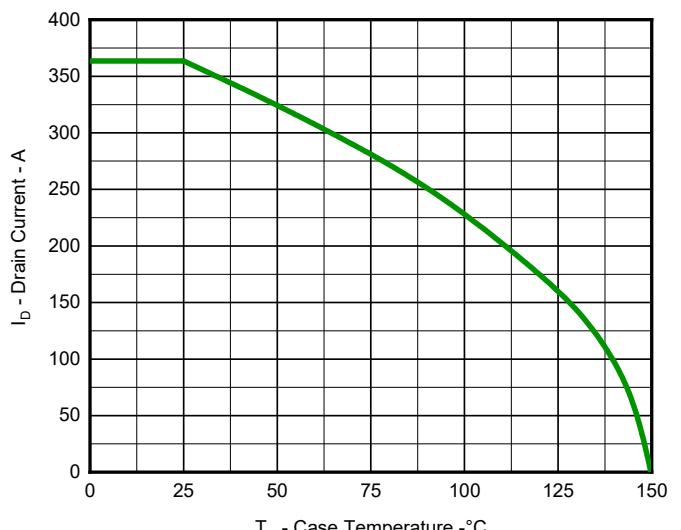


Fig.6 Maximum Drain Current vs. Case Temperature

N-Channel MOSFET

PSMTL04R1L

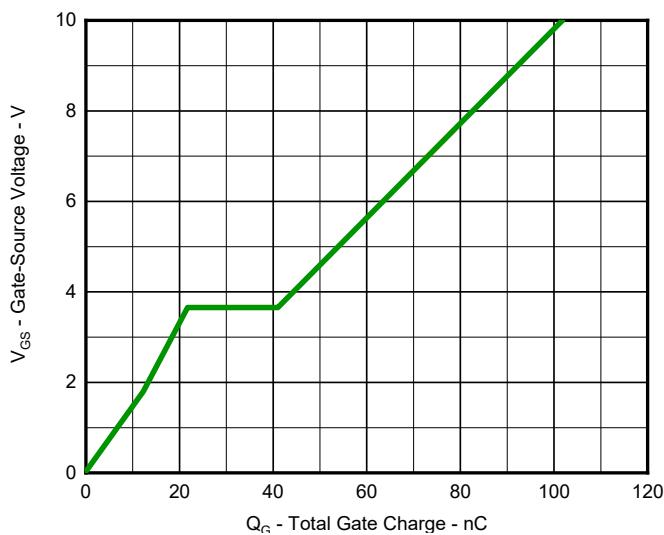


Fig.7 Gate Charge Characteristics

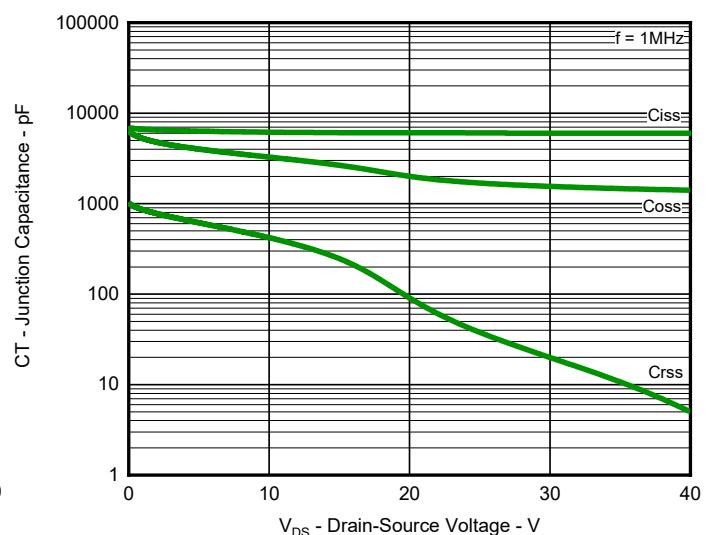


Fig.8 Typical Junction Capacitance

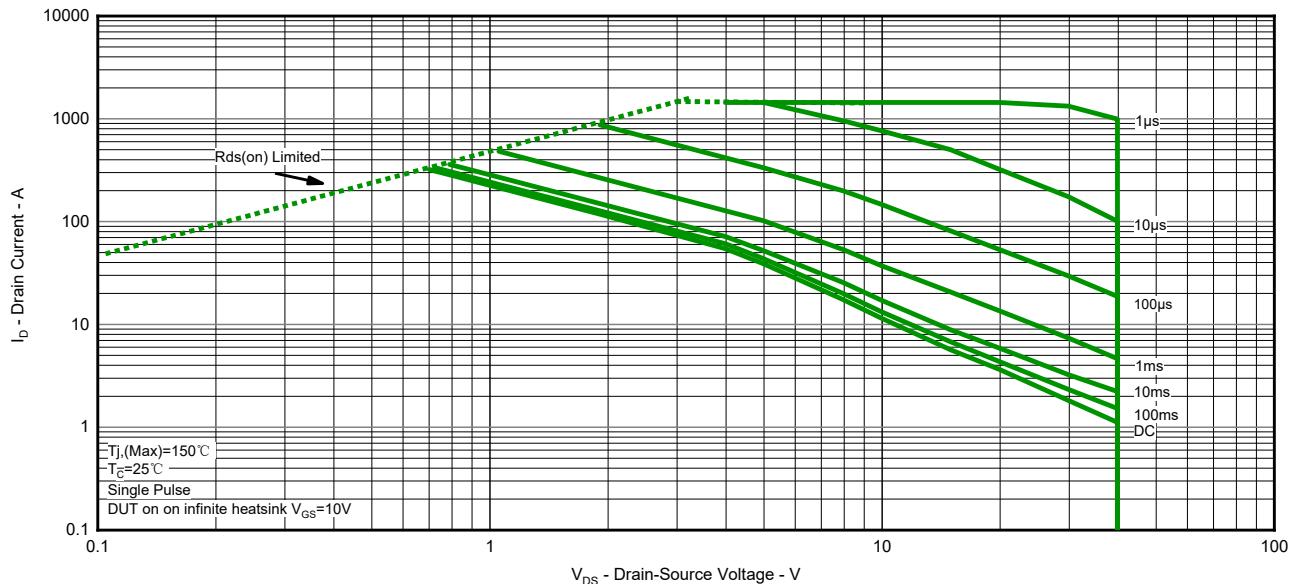


Fig.9 Safe Operation Area

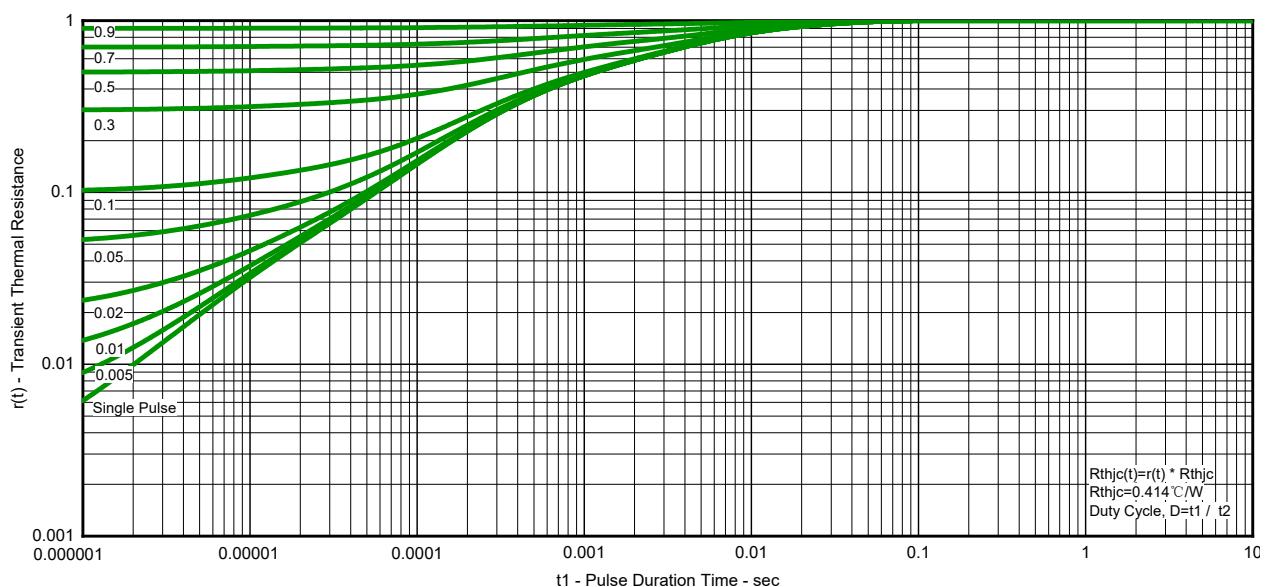
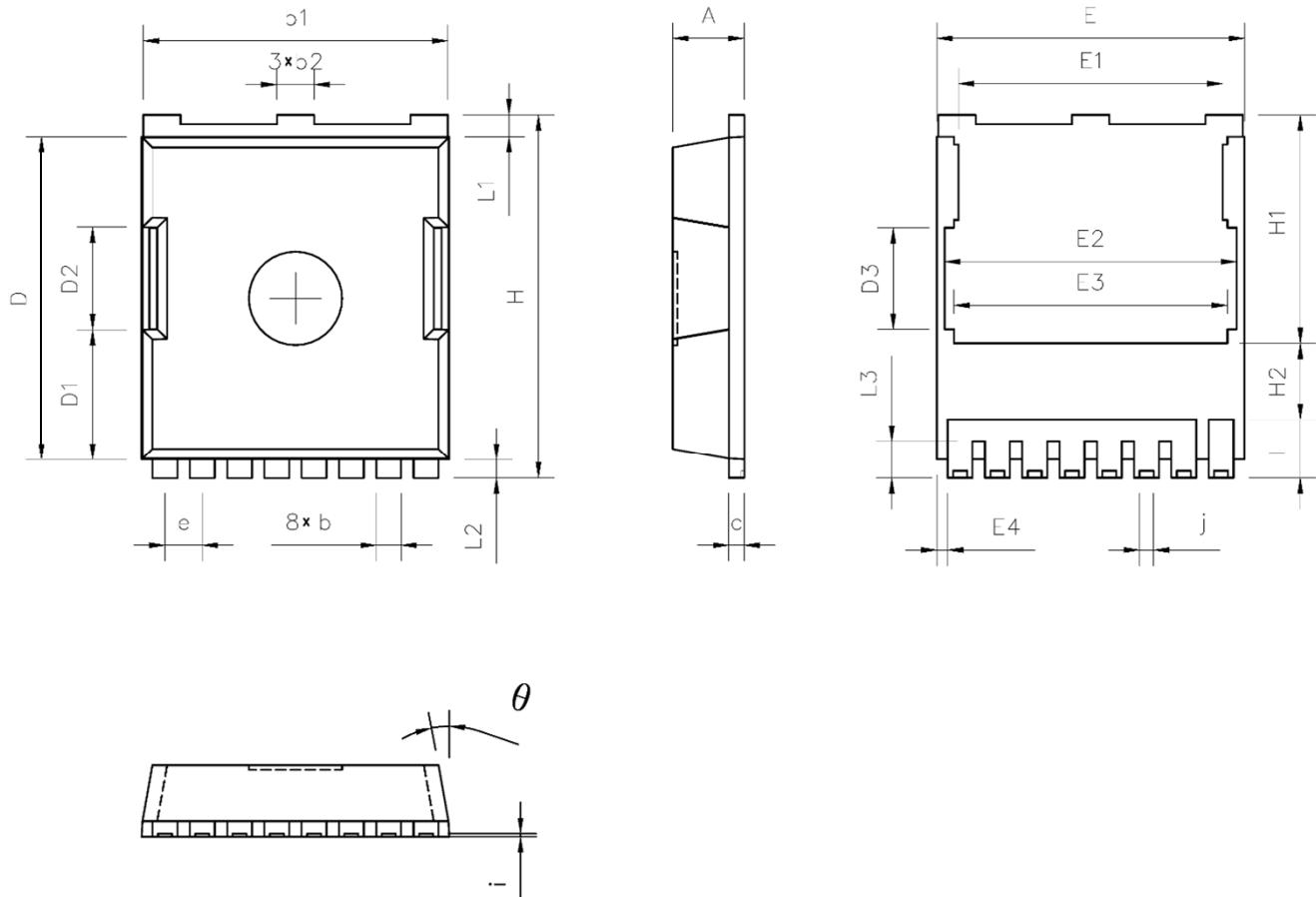


Fig.10 Transient Thermal Resistance

N-Channel MOSFET

PSMTL04R1L

Product Dimension (TOLL-8L)

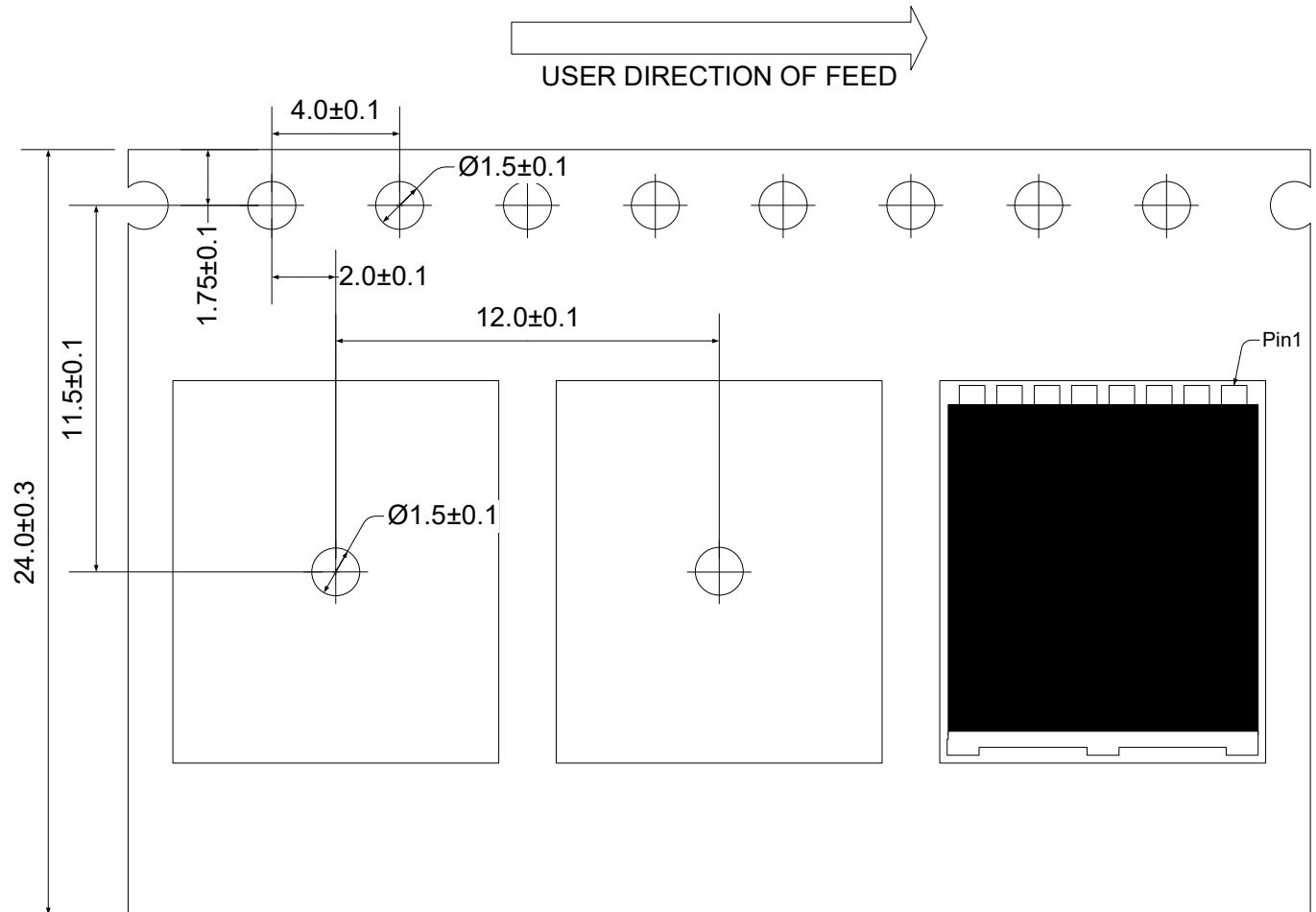


Dim	Millimeters		Inches		Dim	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	2.20	2.40	0.087	0.094	E4	0.25	0.45	0.010	0.018
b	0.70	0.90	0.028	0.035	e	1.20 Basic		0.047 Basic	
b1	9.70	9.90	0.382	0.390	H	11.58	11.78	0.456	0.464
b2	1.20 Ref.		0.047 Ref.		H1	7.23	7.43	0.285	0.293
c	0.40	0.60	0.016	0.024	H2	2.45 Ref.		0.096	Ref.
D	10.28	10.48	0.405	0.413	i	0.10	-	0.004	-
D1	4.06	4.28	0.160	0.169	j	0.45 Ref.		0.018 Ref.	
D2	3.20	3.40	0.126	0.134	L	1.60	2.10	0.063	0.083
D3	3.16	3.36	0.124	0.132	L1	0.60	0.80	0.024	0.031
E	9.80	10.00	0.386	0.394	L2	0.50	0.70	0.020	0.028
E1	8.40	8.60	0.331	0.339	L3	1.05	1.30	0.041	0.051
E2	9.30	9.50	0.366	0.374	θ	10° Ref.		10° Ref.	
E3	8.80 Ref.		0.346 Ref.						

Ordering Information

Device	Package	Reel	Shipping
PSMTL04R1L	TOLL-8L	13"	2000 / Tape & Reel

Load With Information



Unit:mm

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